

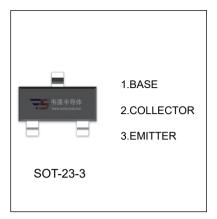
BC807 TRANSISTOR (PNP)

FEATURE

- Ldeally suited for automatic insertion
- Epitaxial planar die construction
- Complementary NPN type available(BC817)

MAXIMUM RATINGS (T₂=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	-50	V	
V _{CEO}	Collector-Emitter Voltage	-45	V	
V _{EBO}	Emitter-Base Voltage	-5	V	
Ic	Collector Current	-500	mA	
Pc	Collector Power Dissipation	300	mW	
R _{OJA}	Thermal Resistance From Junction To Ambient	417	°C/W	
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C	



ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C = -10μA, I _E =0	-50		V
Collector-emitter breakdown voltage	V _{CEO}	I _C = -10mA, I _B =0	-45		V
Emitter-base breakdown voltage	V _{EBO}	I _E = -1μΑ, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} = -45V, I _E =0		-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4 V, I _C =0		-0.1	μA
DC current gain	hFE(1)	V _{CE} = -1V, I _C = -100mA	100	600	
•	hFE(2)	V _{CE} = -1V, I _C = -500mA	40		
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =-500mA, I _B = -50mA		-0.7	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C = -500mA, I _B = -50mA		-1.2	V
Transition frequency	f _T	V _{CE} = -5V, I _C = -10mA f=100MHz	100		MHz

CLASSIFICATION OF h_{FE (1)}

Rank	BC807-16	BC807-25	BC807-40
Range	100-250	160-400	250-600
Marking	5A	5B	5C



